

## General Description

The WSF80N06H uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

## Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

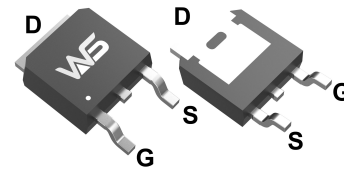
## Product Summary

BVDSS	RDSON	ID
60V	9.1mΩ	80A

## Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

## TO-252 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	50	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	300	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	450	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	110	W
$T_J$ $T_{STG}$	Operating Junction Temperature Range	-55 to 175	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	0.57	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.057	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	9.1	11.5	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	2.0	3.0	4.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.68	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =15A	20	---	---	S
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =30V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =30A	---	36	45	nC
Q <sub>gs</sub>	Gate-Source Charge		---	9.9	18	
Q <sub>gd</sub>	Gate-Drain Charge		---	6.6	15	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =2A, R=1Ω.	---	16	28	ns
T <sub>r</sub>	Rise Time		---	10	21	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	45	65	
T <sub>f</sub>	Fall Time		---	12	22	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	---	2350	---	pF
C <sub>oss</sub>	Output Capacitance		---	237	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	205	---	

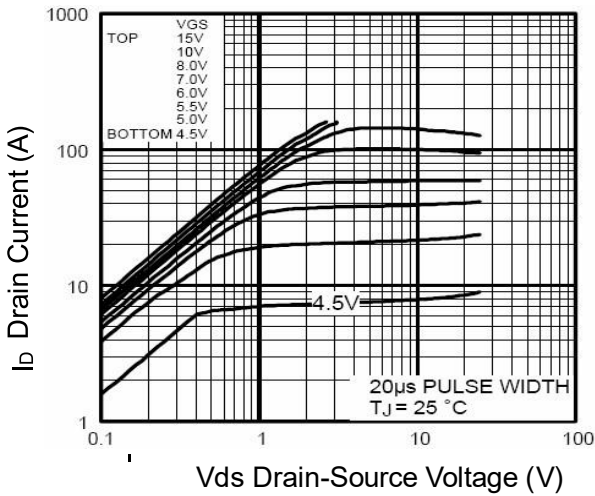
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	80	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	IF=80A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	28	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	49	---	nC

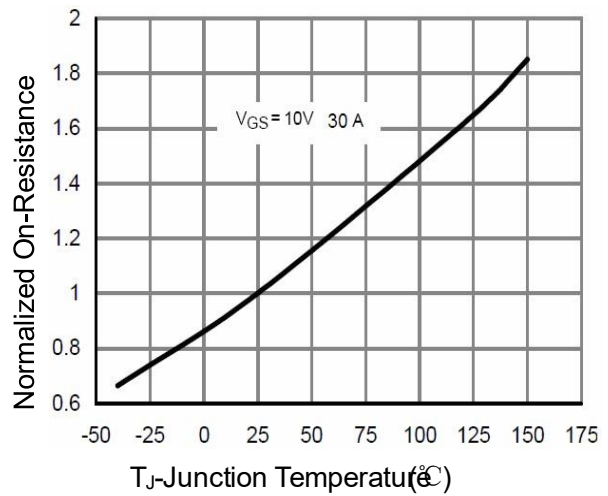
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E<sub>AS</sub> condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=30V, V<sub>G</sub>=10V, L=0.5mH, R<sub>g</sub>=25Ω

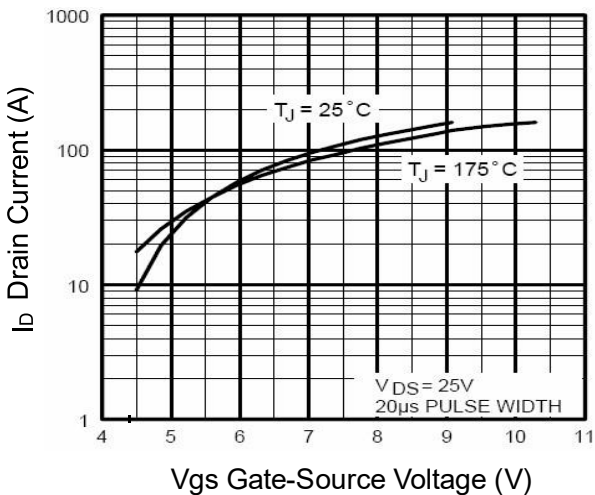
**Typical Characteristics**



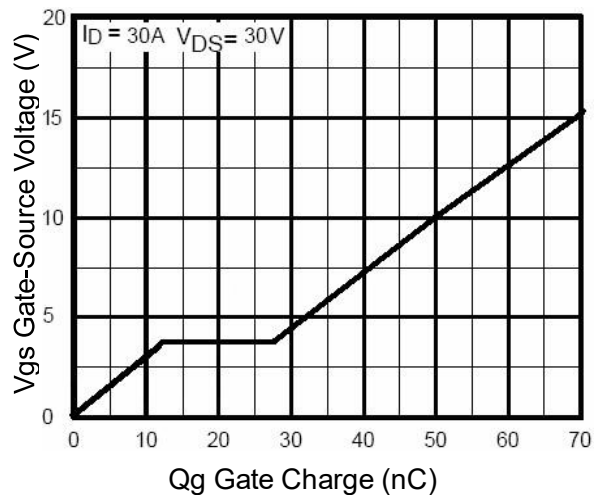
**Figure 1 Output Characteristics**



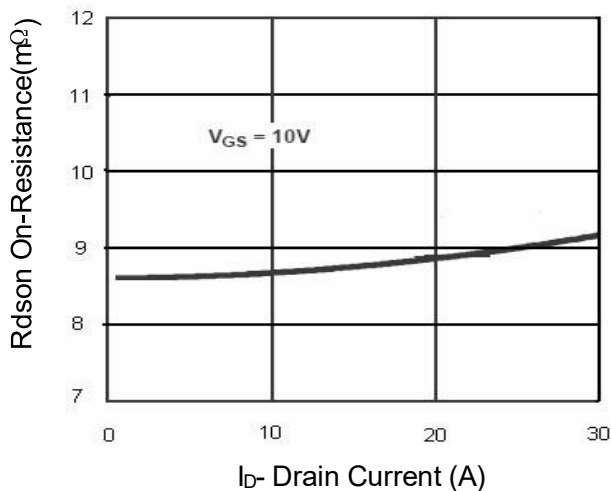
**Figure 4 Rdson-Junction Temperature**



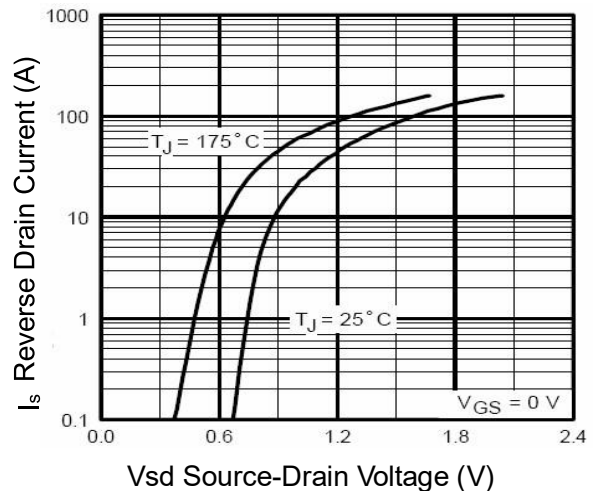
**Figure 2 Transfer Characteristics**



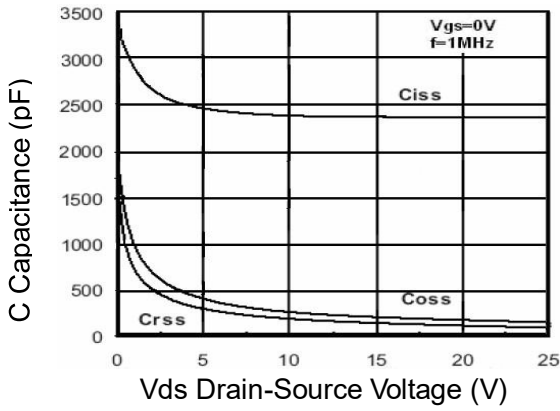
**Figure 5 Gate Charge**



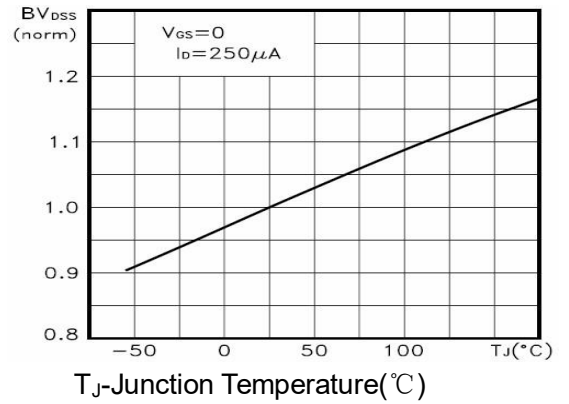
**Figure 3 Rdson Drain Current**



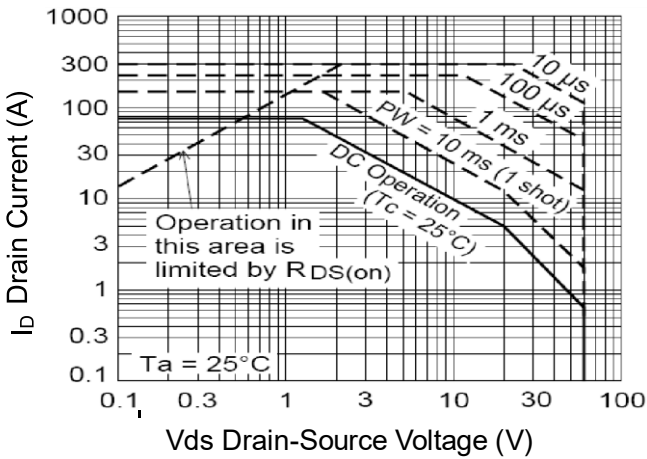
**Figure 6 Source-Drain Diode Forward**



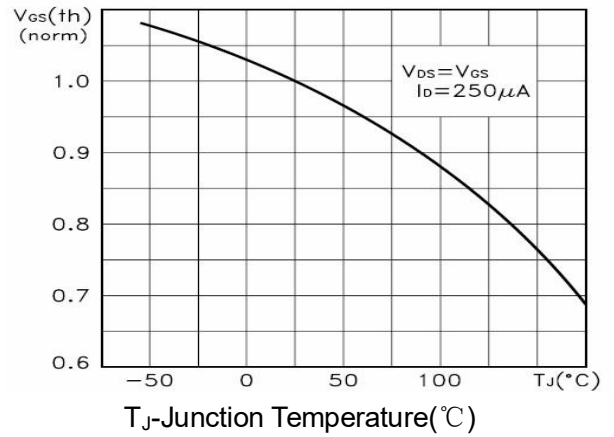
**Figure 7 Capacitance vs Vds**



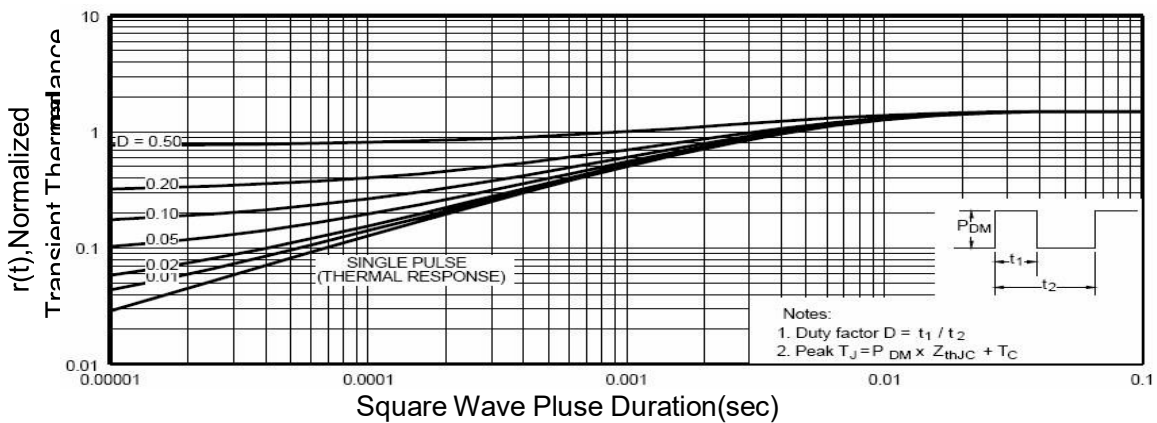
**Figure 9 BV<sub>DSS</sub> vs Junction Temperature**



**Figure 8 Safe Operation Area**



**Figure 10 V<sub>GS(th)</sub> vs Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**



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